



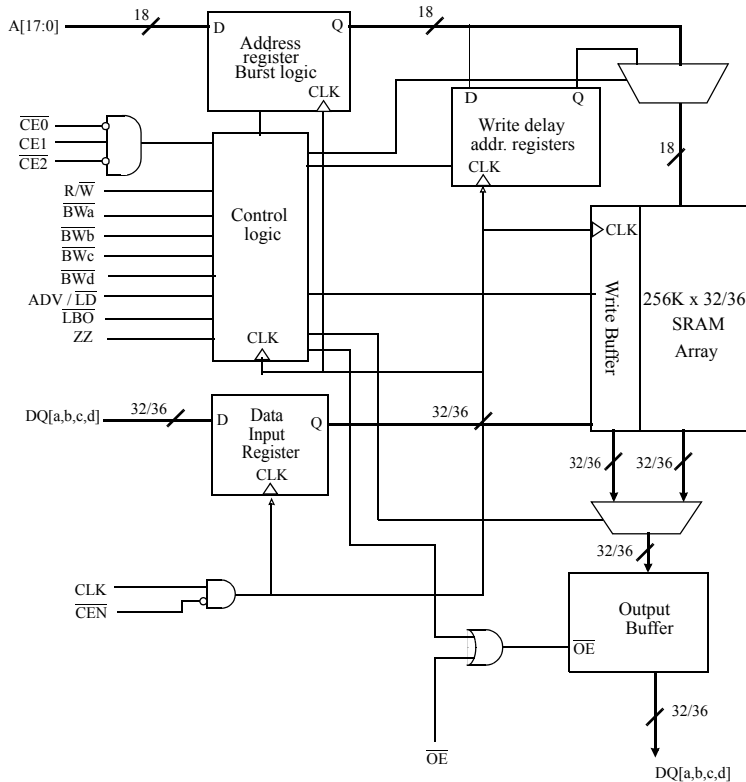
3.3V 256K×32/36 Flowthrough Synchronous SRAM with NTD™

Features

- Organization: 262,144 words × 32 or 36 bits
- NTD™¹ architecture for efficient bus operation
- Fast clock to data access: 6.5/7.5 ns
- Fast OE access time: 3.5 ns
- Fully synchronous operation
- Flow-through mode
- Asynchronous output enable control
- Available in 100-pin TQFP
- Byte write enables
- Clock enable for operation hold
- Multiple chip enables for easy expansion
- 3.3 core power supply
- 2.5V or 3.3V I/O operation with separate V_{DDQ}
- 30 mW typical standby power
- Self-timed write cycles
- Interleaved or linear burst modes
- Snooze mode for standby operation

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Logic Block Diagram

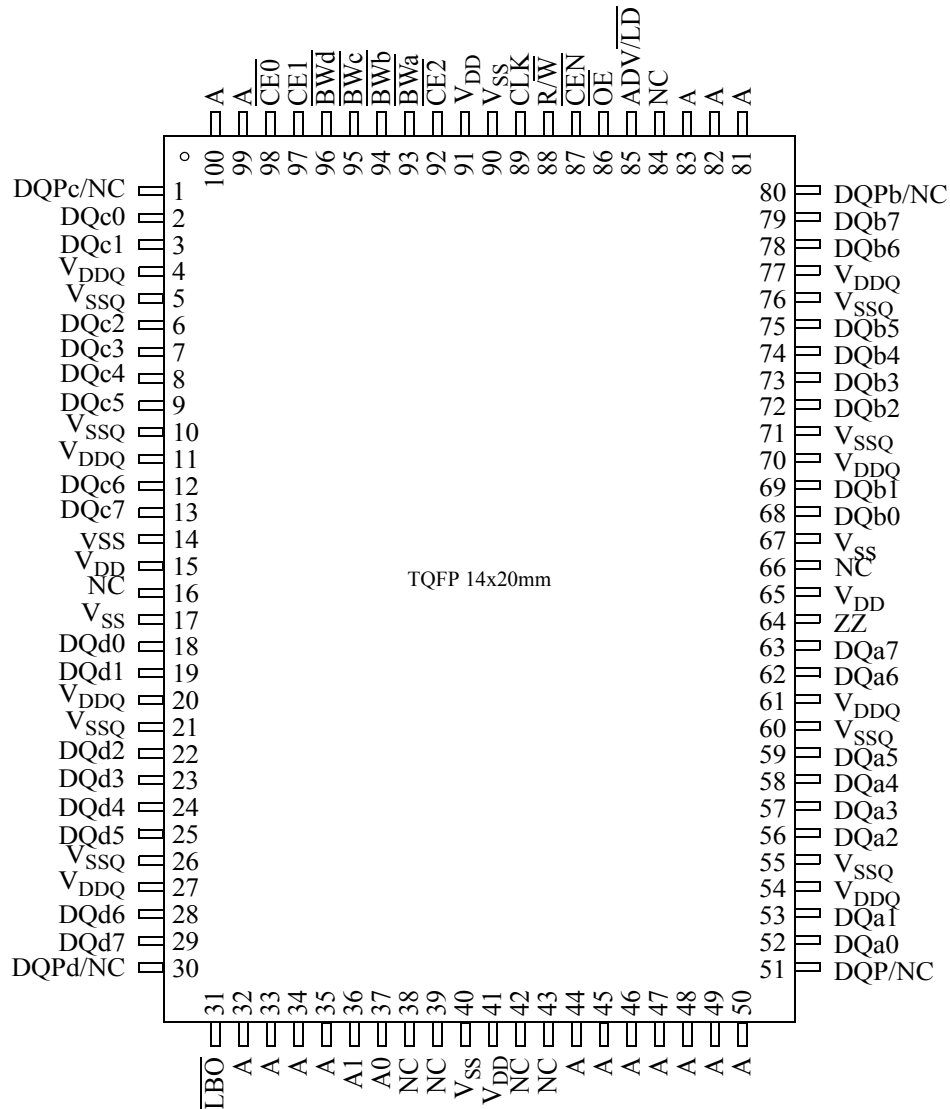


Selection Guide

| | -65 | -75 | Units |
|-----------------------------------|-----|-----|-------|
| Minimum cycle time | 7.5 | 8.5 | ns |
| Maximum clock access time | 6.5 | 7.5 | ns |
| Maximum operating current | 250 | 225 | mA |
| Maximum standby current | 120 | 100 | mA |
| Maximum CMOS standby current (DC) | 30 | 30 | mA |



Pin arrangement for TQFP (top view)



Note: Pins 1, 30, 51, and 80 are NC for ×32



Functional description

The AS7C33256NTF32A/36A family is a high performance CMOS 8 Mbit synchronous Static Random Access Memory (Flowthrough SRAM) organized as 262,144 words \times 32 or 36 bits and incorporates a LATE Write.

This variation of the 8Mb synchronous SRAM uses the No Turnaround Delay (NTDTM) architecture, featuring an enhanced write operation that improves bandwidth over pipelined burst devices. In a normal flowthrough burst device, the write data, command, and address are all applied to the device on the same clock edge. If a read command follows this write command, the system must wait for one 'dead' cycle for valid data to become available. This dead cycle can significantly reduce overall bandwidth for applications requiring random access or read-modify-write operations.

NTDTM devices use the memory bus more efficiently by introducing a write latency which matches one-cycle flow-through read latency. Write data is applied one cycle after the write command and address, allowing the read pipeline to clear. With NTDTM, write and read operations can be used in any order without producing dead bus cycle.

Assert $\overline{R/\overline{W}}$ low to perform write cycles. Byte write enable controls write access to specific bytes, or can be tied low for full 32/36 bit writes. Write enable signals, along with the write address, are registered on a rising edge of the clock. Write data is applied to the device one clock cycle later. Unlike some asynchronous SRAMs, output enable \overline{OE} does not need to be toggled for write operations; it can be tied low for normal operations. Outputs go to a high impedance state when the device is de-selected by any of the three chip enable inputs.

Use the ADV (burst advance) input to perform burst read, write and deselect operations. When ADV is high, external addresses, chip select, $\overline{R/\overline{W}}$ pins are ignored, and internal address counters increment in the count sequence specified by the \overline{LBO} control. Any device operations, including burst, can be stalled using the $\overline{CEN}=1$, the clock enable input.

The AS7C33256NTF32A and AS7C33256NTF36A operate with a $3.3V \pm 5\%$ power supply for the device core (V_{DD}). DQ circuits use a separate power supply (V_{DDQ}) that operates across 3.3V or 2.5V ranges. These devices are available in a 100-pin 14 \times 20 mm TQFP package

Capacitance

| Parameter | Symbol | Test conditions | Min | Max | Unit |
|-------------------|-----------|-------------------------|-----|-----|------|
| Input capacitance | C_{IN} | $V_{in} = 0V$ | - | 5 | pF |
| I/O capacitance | $C_{I/O}$ | $V_{in} = V_{out} = 0V$ | - | 7 | pF |

TQFP thermal resistance

| Description | Conditions | | Symbol | Typical | Units |
|-----------------------------------------------------------|-------------------------------------------------------------------------------------------------------------|---------|---------------|---------|---------------|
| Thermal resistance (junction to ambient) ¹ | Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/JESD51 | 1-layer | θ_{JA} | 40 | $^{\circ}C/W$ |
| | | 4-layer | θ_{JA} | 22 | $^{\circ}C/W$ |
| Thermal resistance (junction to top of case) ¹ | | | θ_{JC} | 8 | $^{\circ}C/W$ |

¹ This parameter is sampled



Signal descriptions

| Signal | I/O | Properties | Description |
|---------------------------------------------|-----|------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| CLK | I | CLOCK | Clock. All inputs except \overline{OE} , \overline{LBO} , and ZZ are synchronous to this clock. |
| \overline{CEN} | I | SYNC | Clock enable. When de-asserted high, the clock input signal is masked. |
| A, A0, A1 | I | SYNC | Address. Sampled when all chip enables are active and $\overline{ADV}/\overline{LD}$ is asserted. |
| DQ[a,b,c,d] | I/O | SYNC | Data. Driven as output when the chip is enabled and \overline{OE} is active. |
| $\overline{CE0}$, CE1, $\overline{CE2}$ | I | SYNC | Synchronous chip enables. Sampled at the rising edge of CLK, when $\overline{ADV}/\overline{LD}$ is asserted. Are ignored when $\overline{ADV}/\overline{LD}$ is high. |
| $\overline{ADV}/\overline{LD}$ | I | SYNC | Advance or Load. When sampled high, the internal burst address counter will increment in the order defined by the \overline{LBO} input value. (refer to table on page 2) When low, a new address is loaded. |
| R/ \overline{W} | I | SYNC | A high during LOAD initiates a READ operation. A low during LOAD initiates a WRITE operation. Is ignored when $\overline{ADV}/\overline{LD}$ is high. |
| $\overline{BW}[a,b,c,d]$ | I | SYNC | Byte write enables. Used to control write on individual bytes. Sampled along with WRITE command and BURST WRITE. |
| \overline{OE} | I | ASYNCR | Asynchronous output enable. I/O pins are not driven when \overline{OE} is inactive. |
| \overline{LBO} | I | STATIC | Selects Burst mode. When tied to V_{DD} or left floating, device follows Interleaved Burst order. When driven Low, device follows linear Burst order. <i>This signal is internally pulled High.</i> |
| ZZ | I | ASYNCR | Snooze. Places device in low power mode; data is retained. Connect to GND if unused. |
| NC | - | - | No connects. Note that pin 84 will be used for future address expansion to 16Mb density. |

Burst Order

| Interleaved Burst Order $\overline{LBO}=1$ | | | | | Linear Burst Order $\overline{LBO}=0$ | | | | |
|--------------------------------------------|-------|-------|-------|-------|---------------------------------------|-------|-------|-------|-------|
| | A1 A0 | A1 A0 | A1 A0 | A1 A0 | | A1 A0 | A1 A0 | A1 A0 | A1 A0 |
| Starting Address | 0 0 | 0 1 | 1 0 | 1 1 | Starting Address | 0 0 | 0 1 | 1 0 | 1 1 |
| First increment | 0 1 | 0 0 | 1 1 | 1 0 | First increment | 0 1 | 1 0 | 1 1 | 0 0 |
| Second increment | 1 0 | 1 1 | 0 0 | 0 1 | Second increment | 1 0 | 1 1 | 0 0 | 0 1 |
| Third increment | 1 1 | 1 0 | 0 1 | 0 0 | Third increment | 1 1 | 0 0 | 0 1 | 1 0 |



Synchronous truth table^[5,6,7,8,9]

| $\overline{\text{CE0}}$ | CE1 | $\overline{\text{CE2}}$ | $\overline{\text{ADV/LD}}$ | R/W | $\overline{\text{BWn}}$ | $\overline{\text{OE}}$ | $\overline{\text{CEN}}$ | Address source | CLK | Operation | DQ | Notes |
|-------------------------|--------------|-------------------------|----------------------------|--------------|-------------------------|------------------------|-------------------------|----------------|--------|-------------------------------|--------|----------|
| H | X | X | L | X | X | X | L | NA | L to H | DESELECT Cycle | High-Z | |
| X | X | H | L | X | X | X | L | NA | L to H | DESELECT Cycle | High-Z | |
| X | L | X | L | X | X | X | L | NA | L to H | DESELECT Cycle | High-Z | |
| X | X | X | H | X | X | X | L | NA | L to H | CONTINUE DESELECT Cycle | High-Z | 1 |
| L | H | L | L | H | X | L | L | External | L to H | READ Cycle (Begin Burst) | Q | |
| X | X | X | H | X | X | L | L | Next | L to H | READ Cycle (Continue Burst) | Q | 1,10 |
| L | H | L | L | H | X | H | L | External | L to H | NOP/DUMMY READ (Begin Burst) | High-Z | 2 |
| X | X | X | H | X | X | H | L | Next | L to H | DUMMY READ (Continue Burst) | High-Z | 1,2,10 |
| L | H | L | L | L | L | X | L | External | L to H | WRITE CYCLE (Begin Burst) | D | 3 |
| X | X | X | H | X | L | X | L | Next | L to H | WRITE CYCLE (Continue Burst) | D | 1,3,10 |
| L | H | L | L | L | H | X | L | External | L to H | NOP/WRITE ABORT (Begin Burst) | High-Z | 2,3 |
| X | X | X | H | X | H | X | L | Next | L to H | WRITE ABORT (Continue Burst) | High-Z | 1,2,3,10 |
| X | X | X | X | X | X | X | H | Current | L to H | INHIBIT CLOCK | - | 4 |

Key: X = Don't Care, H = HIGH, L = LOW. $\overline{\text{BWn}}$ = H means all byte write signals ($\overline{\text{BWa}}$, $\overline{\text{BWb}}$, $\overline{\text{BWc}}$, and $\overline{\text{BWd}}$) are HIGH. $\overline{\text{BWn}}$ = L means one or more byte write signals are LOW.

Notes:

1 CONTINUE BURST cycles, whether READ or WRITE, use the same control inputs. The type of cycle performed (READ or WRITE) is chosen in the initial BEGIN BURST cycle. A CONTINUE DESELECT cycle can only be entered if a DESELECT CYCLE is executed first.

2 DUMMY READ and WRITE ABORT cycles can be considered NOPs because the device performs no external operation. A WRITE ABORT means a WRITE command is given, but no operation is performed.

3 $\overline{\text{OE}}$ may be wired LOW to minimize the number of control signals to the SRAM. The device will automatically turn off the output drivers during a WRITE cycle. $\overline{\text{OE}}$ may be used when the bus turn-on and turn-off times do not meet an application's requirements.

4 If an INHIBIT CLOCK command occurs during a READ operation, the DQ bus will remain active (Low-Z). If it occurs during a WRITE cycle, the bus will remain in High-Z. No WRITE operations will be performed during the INHIBIT CLOCK cycle.

5 $\overline{\text{BWa}}$ enables WRITES to byte "a" (DQa pins/balls); $\overline{\text{BWb}}$ enables WRITES to byte "b" (DQb pins/balls); $\overline{\text{BWc}}$ enables WRITES to byte "c" (DQc pins/balls); $\overline{\text{BWd}}$ enables WRITES to byte "d" (DQd pins/balls).

6 All inputs except $\overline{\text{OE}}$ and ZZ must meet setup and hold times around the rising edge (LOW to HIGH) of CLK.

7 Wait states are inserted by setting $\overline{\text{CEN}}$ HIGH.

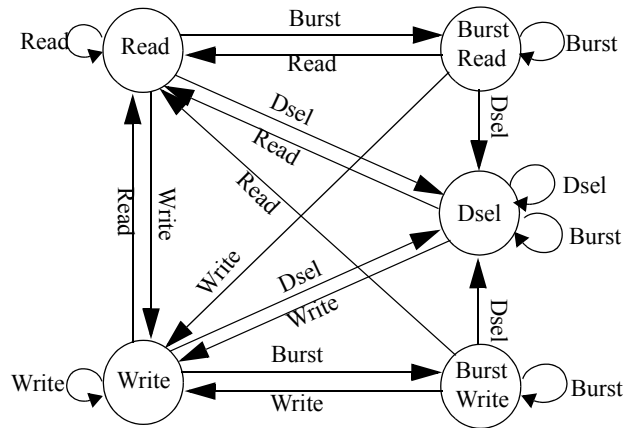
8 This device contains circuitry that will ensure that the outputs will be in High-Z during power-up.

9 The device incorporates a 2-bit burst counter. Address wraps to the initial address every fourth BURST CYCLE.

10 The address counter is incremented for all CONTINUE BURST cycles.



State Diagram for NTD SRAM



Absolute maximum ratings¹

| Parameter | Symbol | Min | Max | Unit |
|--------------------------------------------|-------------------|------|-----------------|------|
| Power supply voltage relative to GND | V_{DD}, V_{DDQ} | -0.5 | +4.6 | V |
| Input voltage relative to GND (input pins) | V_{IN} | -0.5 | $V_{DD} + 0.5$ | V |
| Input voltage relative to GND (I/O pins) | V_{IN} | -0.5 | $V_{DDQ} + 0.5$ | V |
| Power dissipation | P_D | - | 1.8 | W |
| DC output current | I_{OUT} | - | 50 | mA |
| Storage temperature (plastic) | T_{stg} | -65 | +150 | °C |
| Temperature under bias (Junction) | T_{bias} | -65 | +150 | °C |

¹ Stresses greater than those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions outside those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions may affect reliability.

Recommended operating conditions at 3.3V I/O

| Parameter | Symbol | Min | Nominal | Max | Unit |
|---------------------------|-----------|-------|---------|-------|------|
| Supply voltage for inputs | V_{DD} | 3.135 | 3.3 | 3.465 | V |
| Supply voltage for I/O | V_{DDQ} | 3.135 | 3.3 | 3.465 | V |
| Ground supply | V_{SS} | 0 | 0 | 0 | V |

Recommended operating conditions at 2.5V I/O

| Parameter | Symbol | Min | Nominal | Max | Unit |
|---------------------------|-----------|-------|---------|-------|------|
| Supply voltage for inputs | V_{DD} | 3.135 | 3.3 | 3.465 | V |
| Supply voltage for I/O | V_{DDQ} | 2.375 | 2.5 | 2.625 | V |
| Ground supply | V_{SS} | 0 | 0 | 0 | V |



DC electrical characteristics for 3.3V I/O operation

| Parameter | Sym | Conditions | Min | Max | Unit |
|------------------------------------|-----------------|----------------------------------------------------------------------------------------|-------|-----------------------|------|
| Input leakage current ¹ | I _{LI} | V _{DD} = Max, 0V ≤ V _{IN} ≤ V _{DD} | -2 | 2 | μA |
| Output leakage current | I _{LO} | OE ≥ V _{IH} , V _{DD} = Max, 0V ≤ V _{OUT} ≤ V _{DDQ} | -2 | 2 | μA |
| Input high (logic 1) voltage | V _{IH} | Address and control pins | 2 | V _{DD} +0.3 | V |
| | | I/O pins | 2 | V _{DDQ} +0.3 | |
| Input low (logic 0) voltage | V _{IL} | Address and control pins | -0.3* | 0.8 | V |
| | | I/O pins | -0.5* | 0.8 | |
| Output high voltage | V _{OH} | I _{OH} = -4 mA, V _{DDQ} = 3.135V | 2.4 | - | V |
| Output low voltage | V _{OL} | I _{OL} = 8 mA, V _{DDQ} = 3.465V | - | 0.4 | V |

¹ LBO, and ZZ pins have an internal pull-up or pull-down, and input leakage = ±10 μA.

DC electrical characteristics for 2.5V I/O operation

| Parameter | Sym | Conditions | Min | Max | Unit |
|------------------------------|-----------------|----------------------------------------------------------------------------------------|-------|-----------------------|------|
| Input leakage current | I _{LI} | V _{DD} = Max, 0V ≤ V _{IN} ≤ V _{DD} | -2 | 2 | μA |
| Output leakage current | I _{LO} | OE ≥ V _{IH} , V _{DD} = Max, 0V ≤ V _{OUT} ≤ V _{DDQ} | -2 | 2 | μA |
| Input high (logic 1) voltage | V _{IH} | Address and control pins | 1.7 | V _{DD} +0.3 | V |
| | | I/O pins | 1.7 | V _{DDQ} +0.3 | V |
| Input low (logic 0) voltage | V _{IL} | Address and control pins | -0.3* | 0.7 | V |
| | | I/O pins | -0.3* | 0.7 | V |
| Output high voltage | V _{OH} | I _{OH} = -4 mA, V _{DDQ} = 2.375V | 1.7 | - | V |
| Output low voltage | V _{OL} | I _{OL} = 8 mA, V _{DDQ} = 2.625V | - | 0.7 | V |

*V_{IL} min = -1.5 for pulse width less than 0.2 X t_{CYC}

I_{DD} operating conditions and maximum limits

| Parameter | Sym | Conditions | -65 | -75 | Unit |
|---------------------------------------------|------------------|----------------------------------------------------------------------------------------------------------------------------|-----|-----|------|
| Operating power supply current ¹ | I _{CC} | CE0 = V _{IL} , CE1 = V _{IH} , CE2 = V _{IL} , f = f _{Max} , I _{OUT} = 0 mA | 250 | 225 | mA |
| Standby power supply current | I _{SB} | Deselected, f = f _{Max} , ZZ ≤ V _{IL} | 120 | 100 | mA |
| | I _{SB1} | Deselected, f = 0, ZZ ≤ 0.2V, all V _{IN} ≤ 0.2V or ≥ V _{DD} - 0.2V | 30 | 30 | |
| | I _{SB2} | Deselected, f = f _{Max} , ZZ ≥ V _{DD} - 0.2V, all V _{IN} ≤ V _{IL} or ≥ V _{IH} | 30 | 30 | |

¹ I_{CC} given with no output loading. I_{CC} increases with faster cycle times and greater output loading.



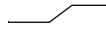
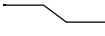

Timing characteristics over operating range

| Parameter | Sym | -65 | | -75 | | Unit | Notes ¹ |
|----------------------------------------------|-------------------|-----|-----|-----|-----|------|--------------------|
| | | Min | Max | Min | Max | | |
| Cycle time | t _{CYC} | 7.5 | - | 8.5 | - | ns | |
| Clock access time | t _{CD} | - | 6.5 | - | 7.5 | ns | |
| Output enable low to data valid | t _{OEL} | - | 3.5 | - | 3.5 | ns | |
| Clock high to output low Z | t _{LZC} | 0.0 | - | 0.0 | - | ns | 2,3,4 |
| Data Output invalid from clock high | t _{OH} | 1.5 | - | 1.5 | - | ns | 2 |
| Output enable low to output low Z | t _{LZOE} | 0.0 | - | 0.0 | - | ns | 2,3,4 |
| Output enable high to output high Z | t _{HZOE} | - | 3.5 | - | 3.5 | ns | 2,3,4 |
| Clock high to output high Z | t _{HZC} | - | 3.5 | - | 3.5 | ns | 2,3,4 |
| Output enable high to invalid output | t _{OHOE} | 0.0 | - | 0.0 | - | ns | |
| Clock high pulse width | t _{CH} | 2.5 | - | 2.5 | - | ns | 5 |
| Clock low pulse width | t _{CL} | 2.5 | - | 2.5 | - | ns | 5 |
| Address and Control setup to clock high | t _{AS} | 1.5 | - | 1.5 | - | ns | 6 |
| Data setup to clock high | t _{DS} | 1.5 | - | 1.5 | - | ns | 6 |
| Write setup to clock high | t _{WS} | 1.5 | - | 1.5 | - | ns | 6, 7 |
| Chip select setup to clock high | t _{CSS} | 1.5 | - | 1.5 | - | ns | 6, 8 |
| Address hold from clock high | t _{AH} | 0.5 | - | 0.5 | - | ns | 6 |
| Data hold from clock high | t _{DH} | 0.5 | - | 0.5 | - | ns | 6 |
| Write hold from clock high | t _{WH} | 0.5 | - | 0.5 | - | ns | 6, 7 |
| Chip select hold from clock high | t _{CSH} | 1.5 | - | 1.5 | - | ns | 6, 8 |
| Clock enable setup to clock high | t _{CENS} | 1.5 | - | 1.5 | - | ns | 6 |
| Clock enable hold from clock high | t _{CENH} | 0.5 | - | 0.5 | - | ns | 6 |
| $\overline{\text{ADV}}$ setup to clock high | t _{ADVS} | 1.5 | - | 1.5 | - | ns | 6 |
| $\overline{\text{ADV}}$ hold from clock high | t _{ADVH} | 0.5 | - | 0.5 | - | ns | 6 |

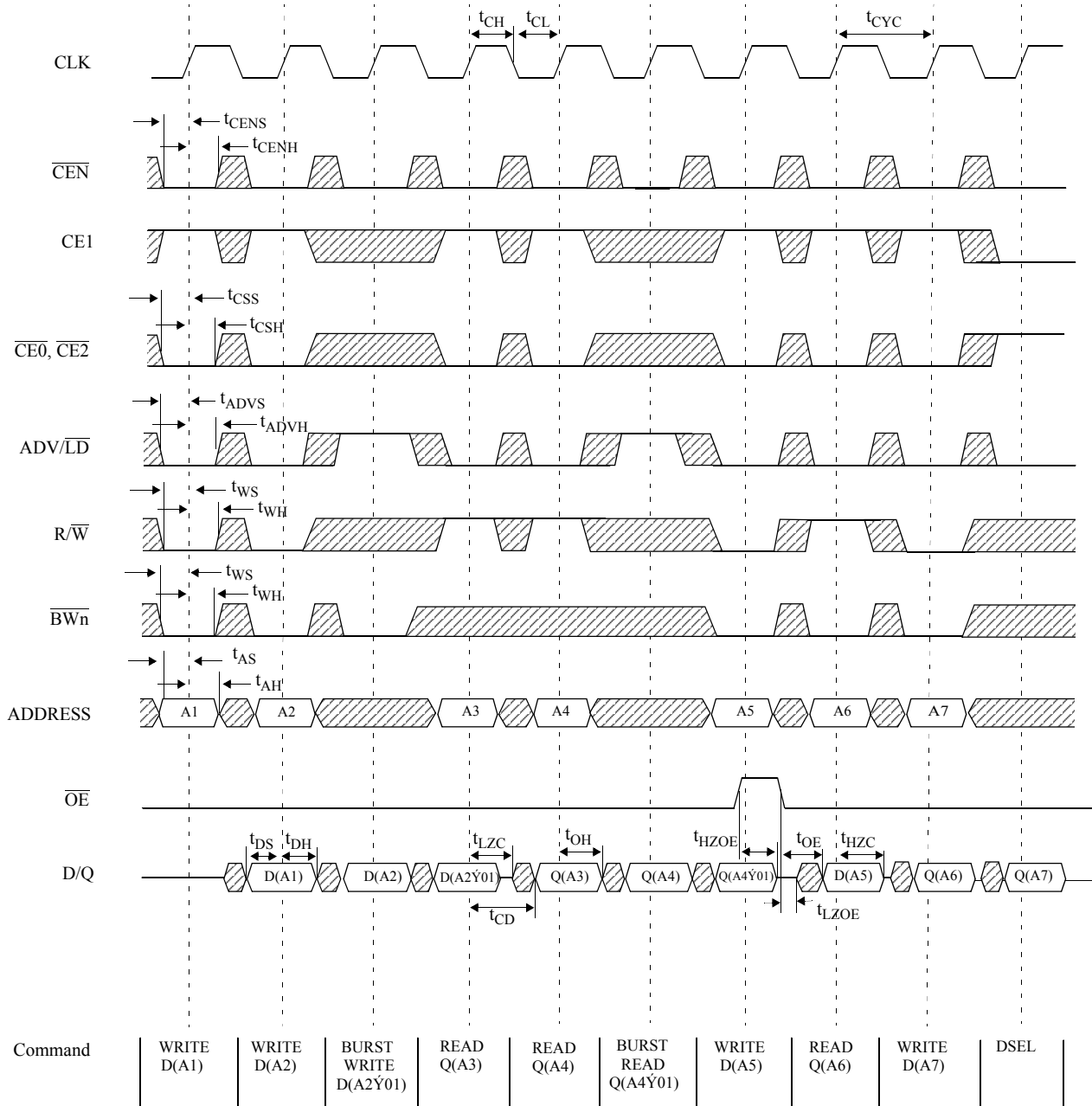
¹ See "Notes" on page 11.



Key to switching waveforms

 Rising input
  Falling input
  Undefined/don't care

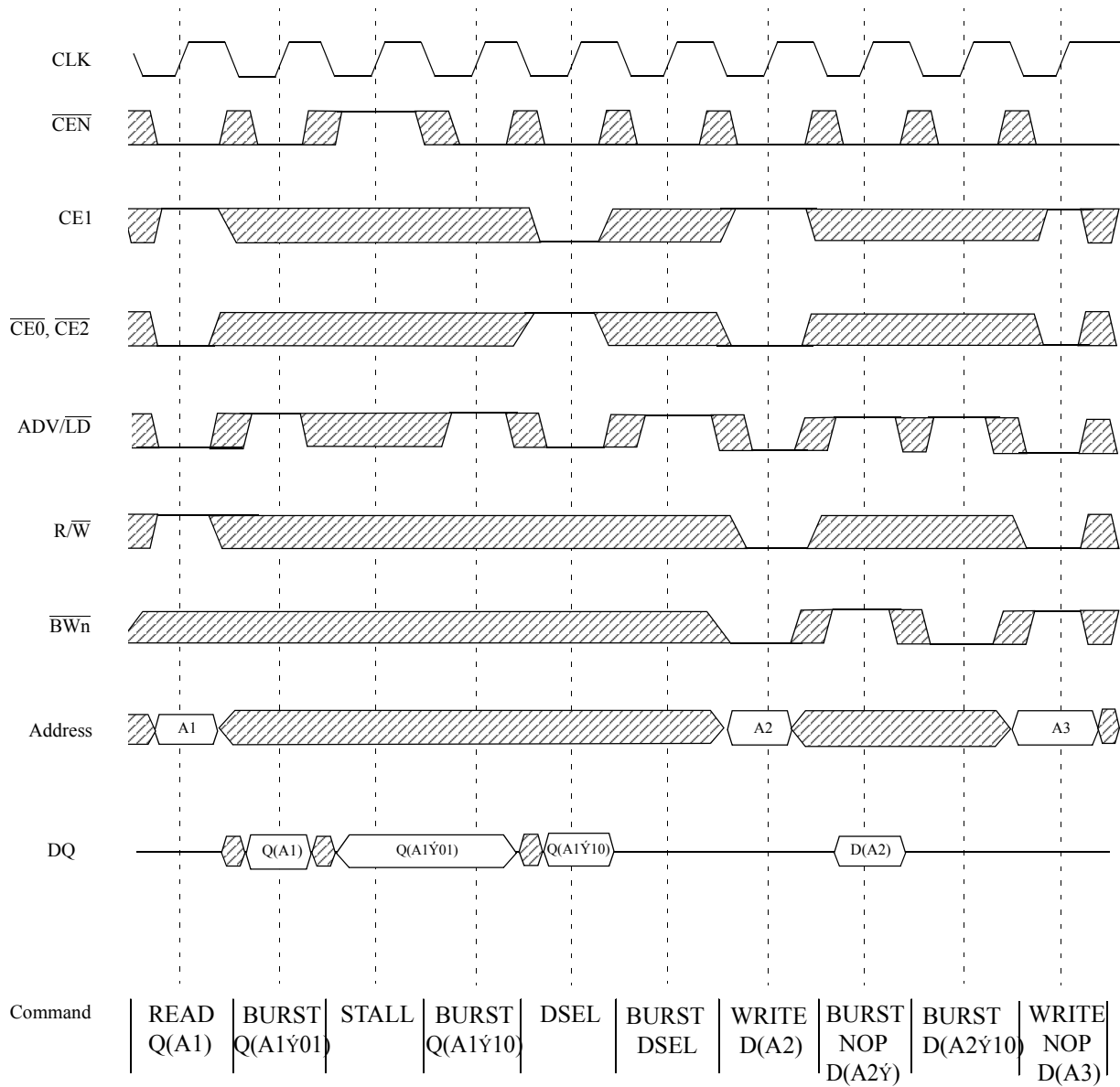
Timing waveform of read/write cycle



Note: \dot{Y} = XOR when $\overline{LB0}$ = high/no connect; \dot{Y} = ADD when $\overline{LB0}$ = low. $\overline{BW[a:d]}$ is don't care.



NOP, stall and deselect cycles



Note: \dot{Y} = XOR when $\overline{LB0}$ = high/no connect; \dot{Y} = ADD when $\overline{LB0}$ = low. \overline{OE} is low.



AC test conditions

- Output Load: see Figure B, except for t_{LZC} , t_{LZOE} , t_{HZOE} , t_{HZC} see Figure C.
- Input pulse level: GND to 3V. See Figure A.
- Input rise and fall time (Measured at 0.3V and 2.7V): 2 ns. See Figure A.
- Input and output timing reference levels: 1.5V.

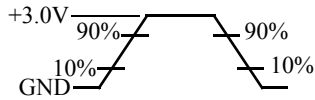


Figure A: Input waveform

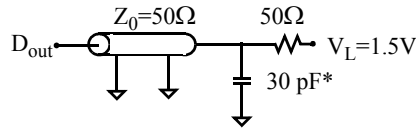


Figure B: Output load (A)

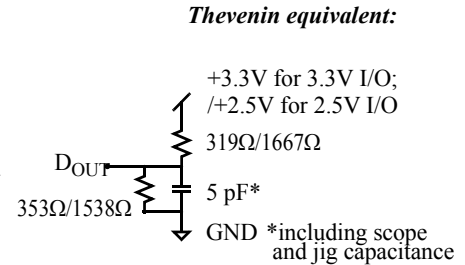


Figure C: Output load(B)

Notes

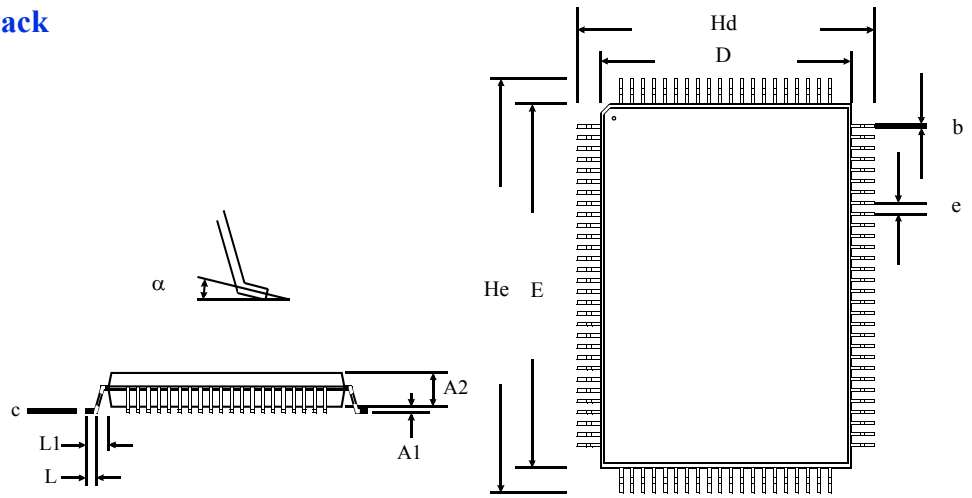
- | | |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| <p>1 For test conditions, see <i>AC Test Conditions</i>, Figures A, B, C.</p> <p>2 This parameter measured with output load condition in Figure C</p> <p>3 This parameter is sampled and not 100% tested.</p> <p>4 t_{HZOE} is less than t_{LZOE}; and t_{HZC} is less than t_{LZC} at any given temperature and voltage.</p> <p>5 t_{HZCN} is a 'no load' parameter to indicate exactly when SRAM outputs have stopped driving.</p> <p>6 I_{CC} given with no output loading. I_{CC} increases with faster cycle times and greater output loading.</p> | <p>7 Transitions are measured ± 500 mV from steady state voltage. Output loading specified with $C_L = 5$ pF as in Figure C.</p> <p>8 t_{CH} measured as high above V_{IH}, and t_{CL} measured as low below V_{IL}</p> <p>9 This is a synchronous device. All addresses must meet the specified setup and hold times for all rising edges of CLK. All other synchronous inputs must meet the setup and hold times with stable logic levels for all rising edges of CLK when chip is enabled.</p> |
|----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|



Package Dimensions

100-pin quad flat pack

| | TQFP | |
|---------------------------|--------------|-------|
| | Min | Max |
| A1 | 0.05 | 0.15 |
| A2 | 1.35 | 1.45 |
| b | 0.22 | 0.38 |
| c | 0.09 | 0.20 |
| D | 13.80 | 14.20 |
| E | 19.80 | 20.20 |
| e | 0.65 nominal | |
| Hd | 15.80 | 16.20 |
| He | 21.80 | 22.20 |
| L | 0.45 | 0.75 |
| L1 | 1.00 nominal | |
| α | 0° | 7° |
| Dimensions in millimeters | | |





Ordering information

| Package | Width | -65 | -75 |
|---------|-------|-----------------------|-----------------------|
| TQFP | x32 | AS7C33256NTF32A-65TQC | AS7C33256NTF32A-75TQC |
| TQFP | x32 | AS7C33256NTF32A-65TQI | AS7C33256NTF32A-75TQI |
| TQFP | x36 | AS7C33256NTF36A-65TQC | AS7C33256NTF36A-75TQC |
| TQFP | x36 | AS7C33256NTF36A-65TQI | AS7C33256NTF36A-75TQI |

Note: Add suffix 'N' to the above part numbers for Lead Free Parts (Ex. AS7C33256NTF32A-65TQCN)

Part numbering guide

| AS7C | 33 | 256 | NTF | 32/36 | A | -XX | TQ | C/I | X |
|------|----|-----|-----|-------|---|-----|----|-----|----|
| 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 |

1. Alliance Semiconductor SRAM prefix
2. Operating voltage: 33 = 3.3V
3. Organization: 256 = 256K
4. NTF = No Turn-around Delay, Flowthrough mode
5. Organization: 32 = x32; 36 = x36
6. Production version: A = first production version
7. Clock speed
8. Package type: TQ = TQFP.
9. Operating temperature: C = commercial (0° C to 70° C); I = industrial (-40° C to 85° C)
10. N = Lead free part



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